

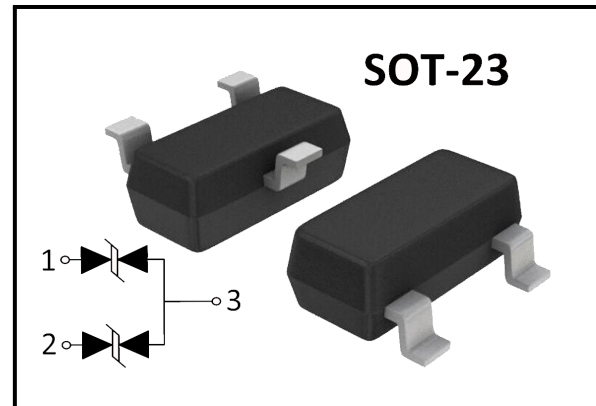
BNPESD2ETH100T

ESD Protection Diode

Features

- 130Watts peak pulse power ($t_p = 8/20\mu s$)
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping Voltage
- Low leakage current
- IEC 61000-4-2 $\pm 25kV$ contact ; $\pm 25kV$ air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 3.5A (8/20 μs)

Package



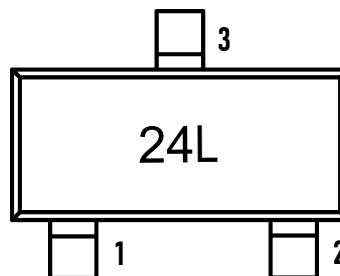
Applications

- Dataline
- Automatic Teller Machines
- Net works
- Power line

Mechanical Characteristics

- SOT-23 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Marking



Ordering information

Order code	Package	Marking	Base qty	Delivery mode
BNPESD2ETH100T	SOT-23	24L	3k	Tape and reel

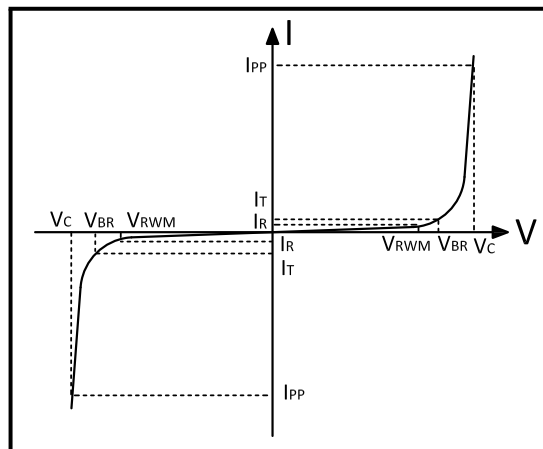


BNPESD2ETH100T

ESD Protection Diode

Electrical Parameters ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current



Note: 8/20us pulse Waveform.

Absolute Maximum Rating

Rating	Symler	Value	Units
Peak Pulse Power ($t_p = 8/20\mu\text{s}$)	P_{PP}	130	Watts
Peak Pulse Current ($t_p = 8/20\mu\text{s}$)	I_{PP}	3.5	A
ESD per IEC 61000-4-2 (Air)	V_{ESD}	25	KV
ESD per IEC 61000-4-2 (Contact)		25	
Lead Soldering Temperature	T_L	260(10seconds)	$^\circ\text{C}$
Junction Temperature	T_J	-55 to + 150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to + 150	$^\circ\text{C}$

Electrical Characteristics

Parameter	Symler	Conditions	Min.	Typical	Max.	Units
Reverse Stand-Off Voltage	V_{RWM}	—	—	—	24.0	V
Reverse Breakdown Voltage	V_{BR}	$I_T = 1\text{mA}$	26.7	28	32.0	V
Reverse Leakage Current	I_R	$V_{RWM} = 24\text{V}, T = 25^\circ\text{C}$	—	—	0.5	μA
Peak Pulse Current	I_{PP}	$t_p = 8/20\mu\text{s}$	—	—	3.5	A
Clamping Voltage	V_C	$I_{PP} = 3.5\text{A}, t_p = 8/20\mu\text{s}$	—	36	38	V
Junction Capacitance	C_j	$V_R = 0\text{V}, T = 25^\circ\text{C}, f = 1\text{MHz}$ (Pin1, Pin2 to Pin3)	—	1.20	1.60	pF
Junction Capacitance	C_j	$V_R = 0\text{V}, T = 25^\circ\text{C}, f = 1\text{MHz}$ (Pin1 to Pin2)	—	0.60	0.80	pF

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Revision: 2022-Jan-1-A



Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

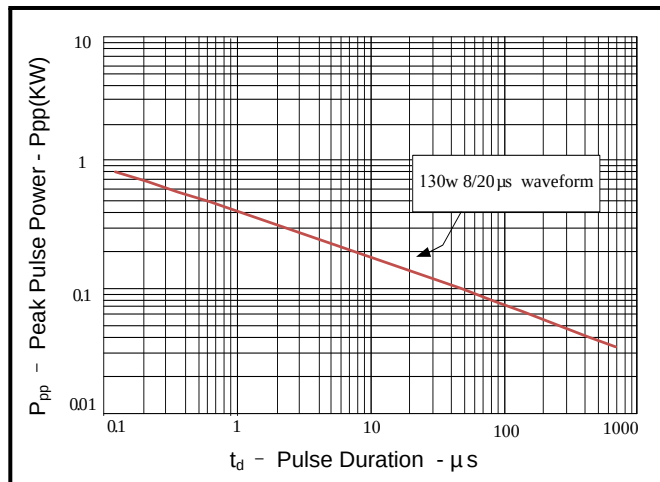


Figure 2: Power Derating Curve

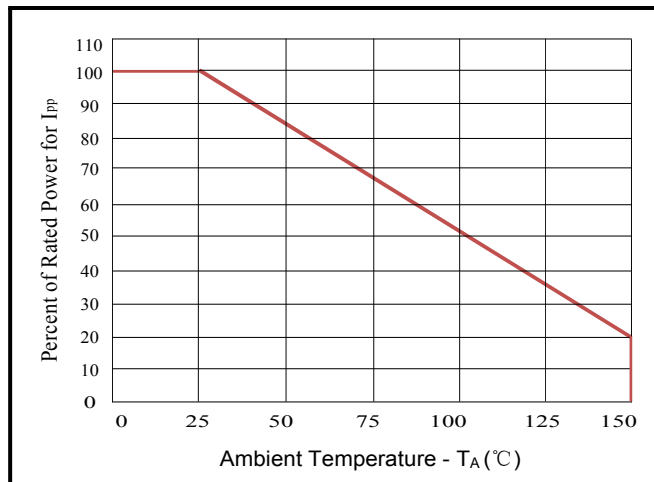


Figure 3: Pulse Waveform

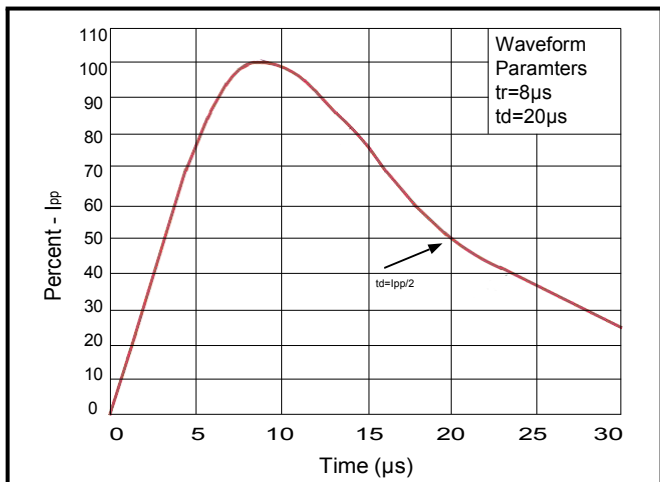
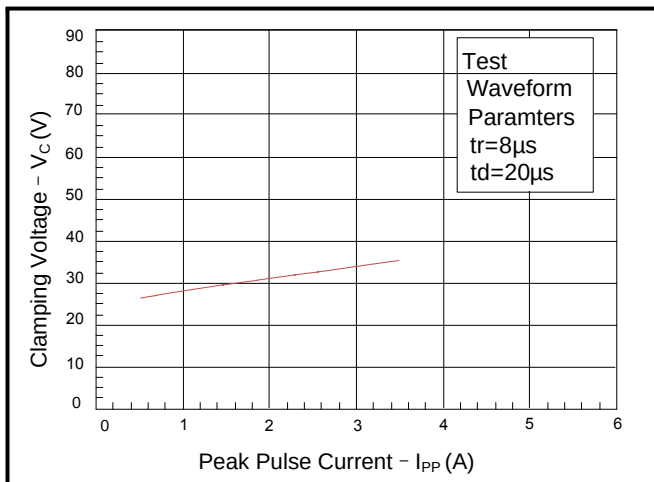


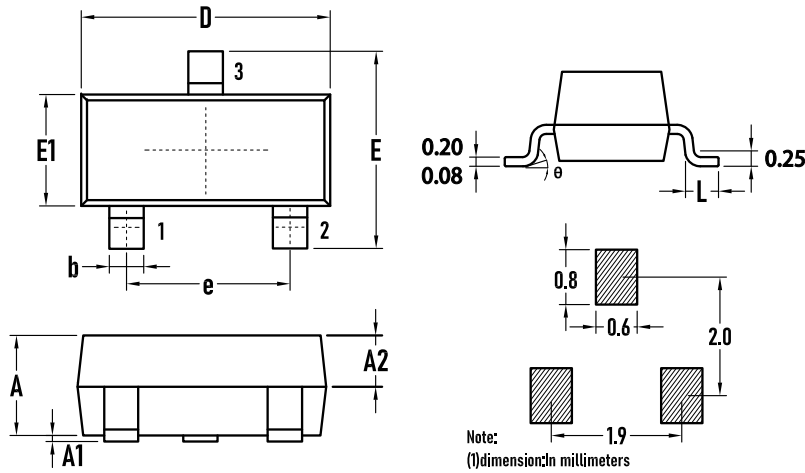
Figure 4: Clamping Voltage vs. IPP



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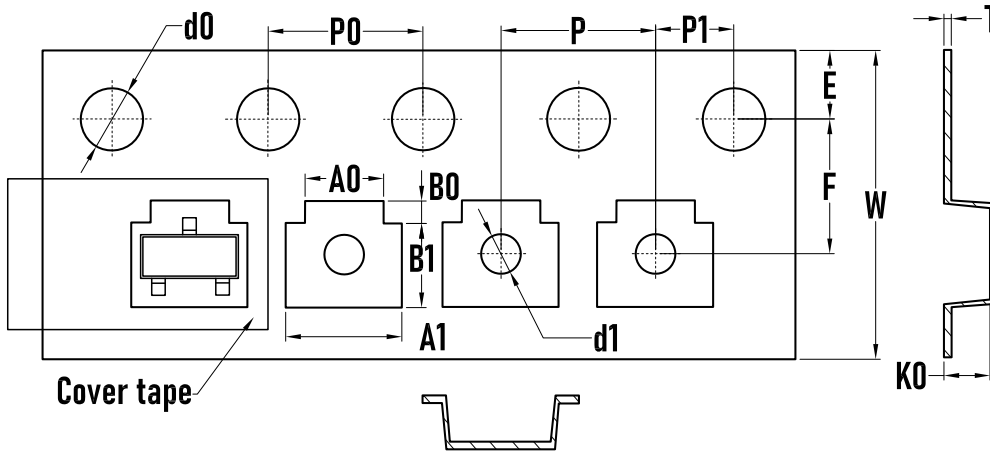
ESD Protection Diode

Outline Drawing – SOT-23



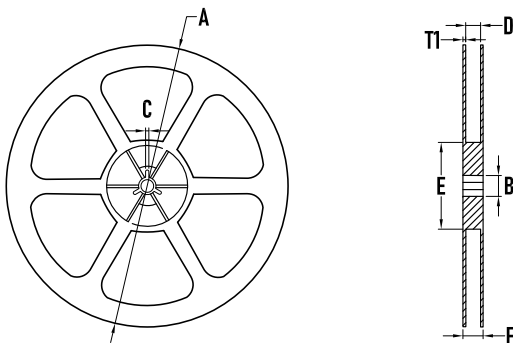
SYMBOL	MILLIMETER		
	MIN.	Typ.	MAX.
A	0.90	1.00	1.10
A1	0.01	—	0.10
A2	0.50	0.60	0.70
D	2.80	2.90	3.00
b	0.25	0.35	0.45
E	2.10	2.30	2.50
E1	1.20	1.30	1.40
e	1.80	1.90	2.00
L	0.25	0.35	0.45
θ	0	—	8°

Packaging Tape - SOT-23



SYMBOL	MILLIMETER
A0	2.10±0.10
A1	3.10±0.10
B0	0.65±0.10
B1	2.75±0.10
d0	1.55±0.10
d1	1.00±0.05
E	1.75±0.10
F	3.50±0.10
K0	1.10±0.10
P	4.00±0.10
P0	4.00±0.10
P1	2.00±0.10
W	8.00±0.30
T	0.20 ±0.05

Packaging Reel



SYMBOL	MILLIMETER
A	177.8±0.2
B	3.1
C	13.50
D	9.6±0.3
E	75±0.2
F	12.3±0.3
T1	1.0±0.2
Quantity	3000PCS

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